

Reducing Residual Resistance at Operating Fields: Potential, Challenges, and Future R&D Directions

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 **Jefferson Lab**



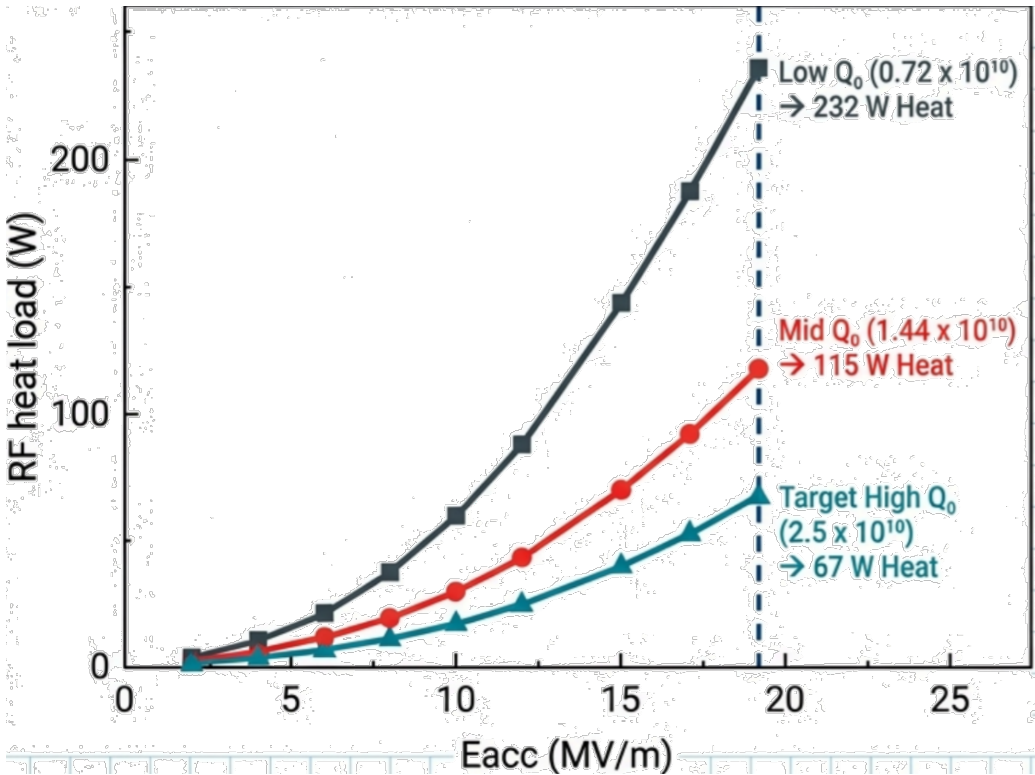
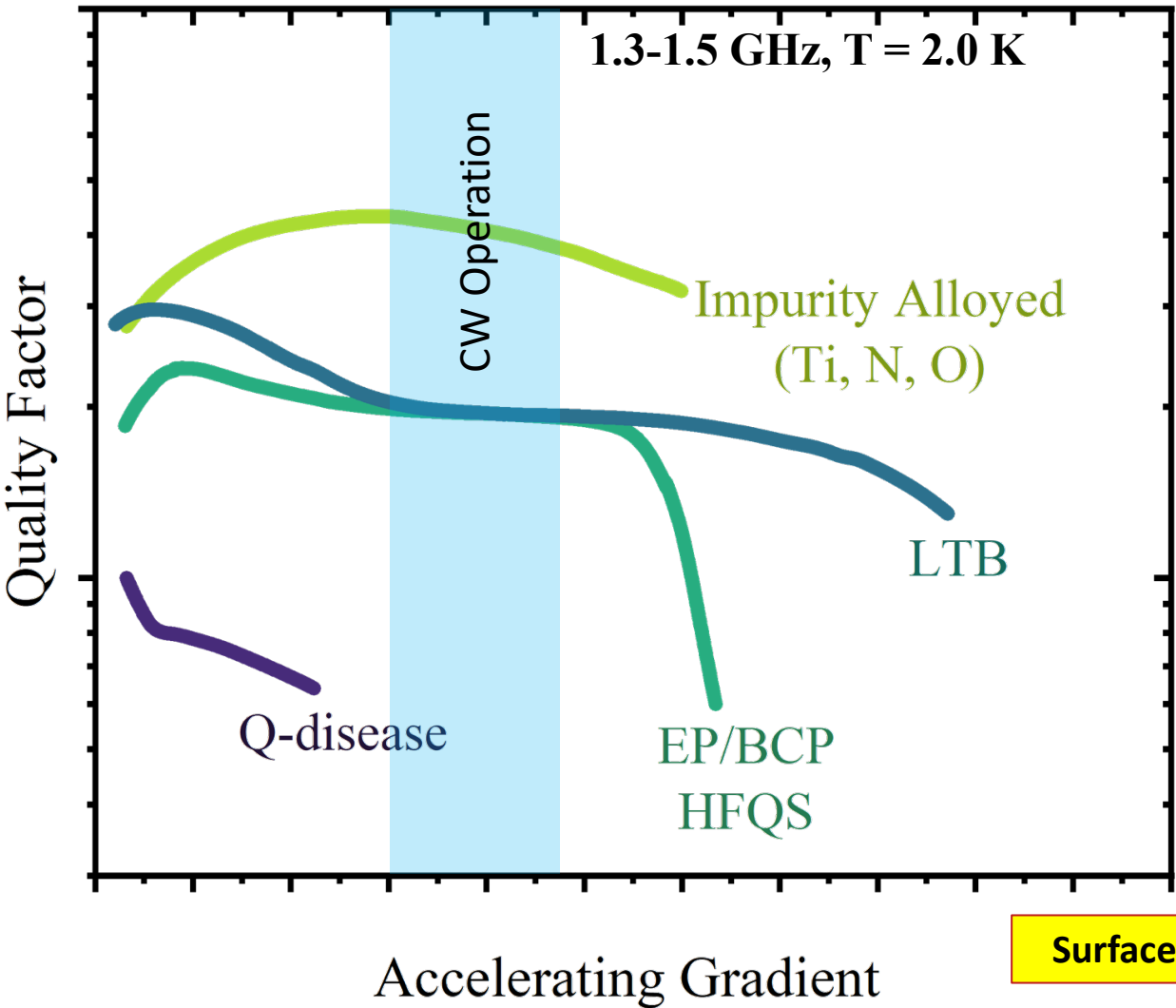
U.S. DEPARTMENT
of **ENERGY**



- Current Status of SRF R&D
- High Q, High Gradient
- Potential, Challenges, and Future R&D Directions

CURRENT STATUS OF SRF R&D




$$P_{RF} = (E_{acc})^2 \left(\frac{R_s}{G} \right) \left(\frac{1}{R/Q} \right)$$

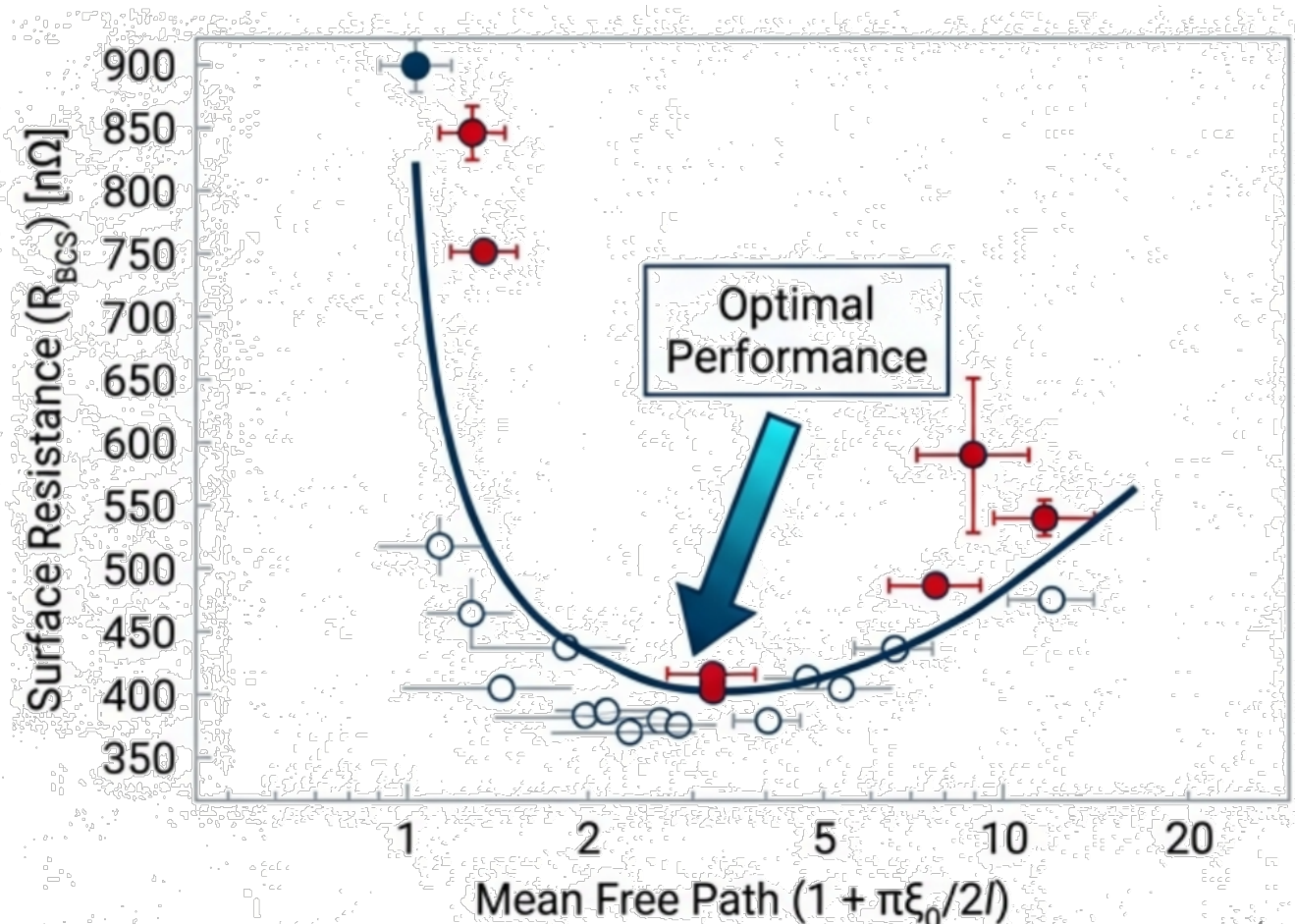


Surface resistance is not just a material parameter; it is an operating expense.

SURFACE RESISTANCE

$$R_s(T, B_{rf}) = R_{BCS}(T, B_{rf}) + R_o(B_{rf})$$

- **Counter-Intuitive Physics:**  Pure Niobium is not the theoretical optimum.
- **The Mechanism:**  By introducing impurities (doping), we shorten the electron mean free path.
- **The Result:**  Resistance reaches a minimum when the coherence length matches the mean free path ($\xi_0/\ell \approx 1$).



RESIDUAL RESISTANCE (R_0)

$R_{\text{interstitial}}$: Caused by material impurities (H, N, C). Addressed by high RRR.

$R_{\text{interface}}$: Substrate effects, typically for bi-metallic structures.

R_{suboxide} : Surface oxides (NbO_2 , NbO). Addressed by annealing.

$$R_0 = R_{\text{interstitial}} + R_{\text{suboxide}} + R_{\text{TLS}} + R_{\text{interface}} + R_{\text{flux}} + R_{\text{surfacedefects}} + \dots$$

R_{TLS} : Two-Level Systems due to Nb_2O_5 (at $T < 1$ K). Addressed by Annealing/Capping.

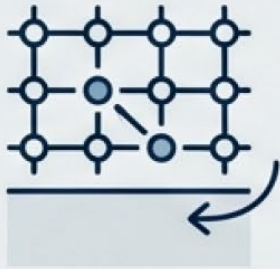
$R_{\text{surface defects}}$: Surface damage. Addressed by Chemical/Mechanical Polishing.

R_{flux} : Trapped Flux. Addressed by shielding and cooldown protocols.

HIGH Q_0 , HIGH GRADIENT

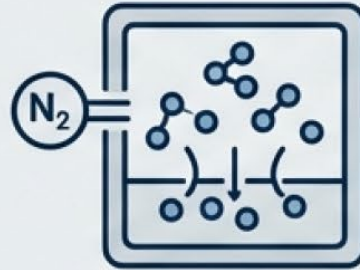
The Recipe: Surface Alloying within the RF Penetration Depth

Titanium Doping



Surface alloying with Ti.

Nitrogen Doping/Infusion



High-temperature furnace treatment with N_2 gas.

Oxygen (Mid-T Bake)



Baking at 300°C–400°C to diffuse native oxide layers.



➤ Q-rise is due to the current-induced broadening of the quasiparticle density of states in dirty limit.

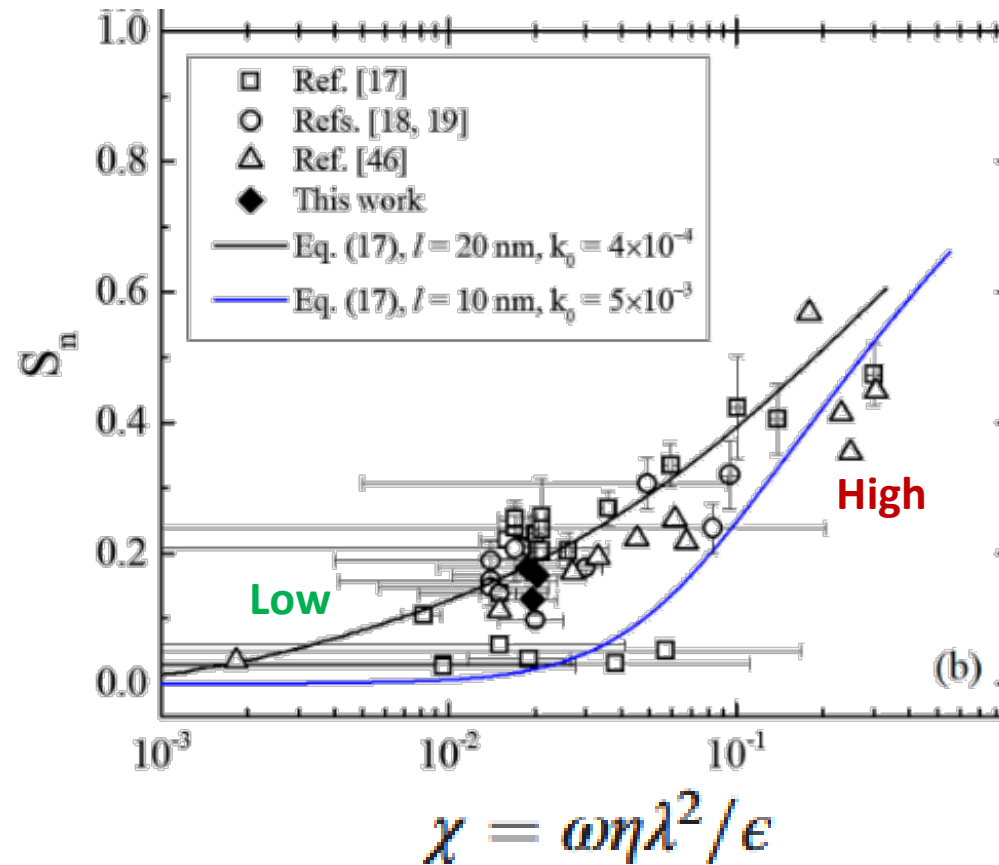
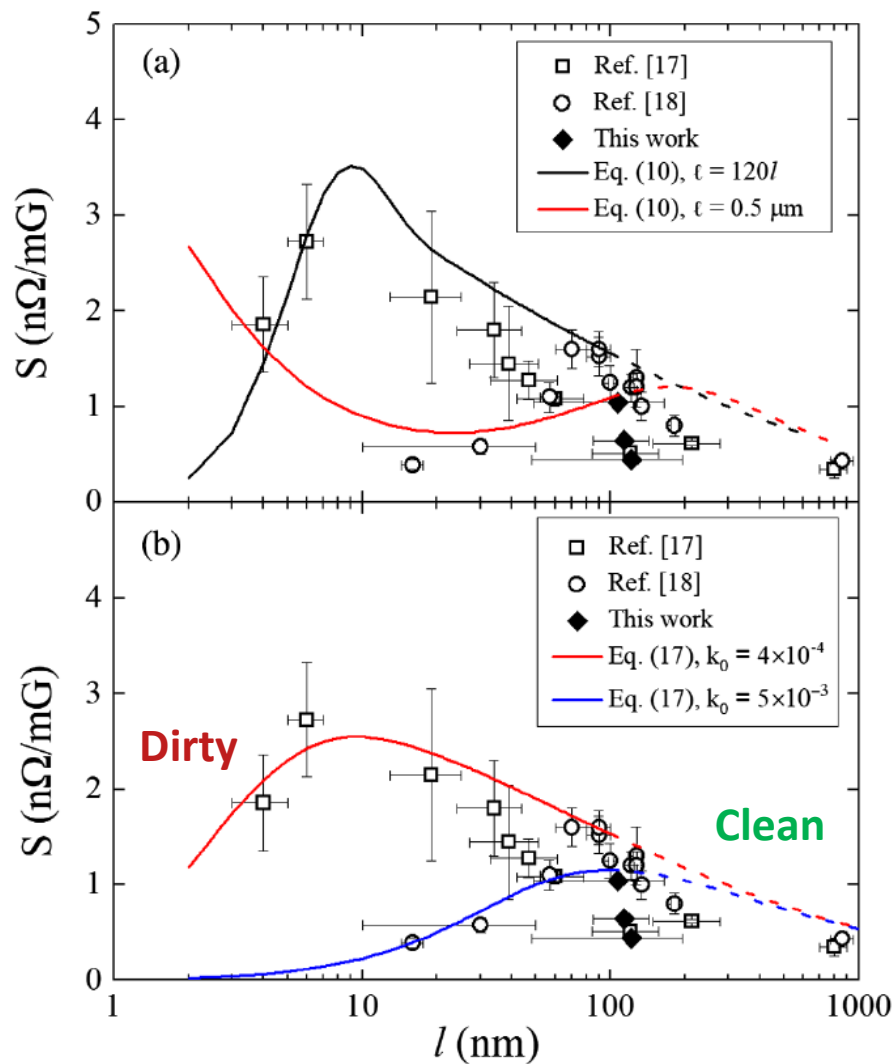
Gurevich, PRL 2014

➤ High Q_0 cavities are very sensitive to trapped magnetic flux during cooldown, often mask the benefit of high Q_0

RESIDUAL RESISTANCE (R_0)

$$R_0 = R_{\text{interstitial}} + R_{\text{suboxide}} + R_{\text{TLS}} + R_{\text{interface}} + R_{\text{flux}} + R_{\text{surfacedefects}} + \dots$$

FLUX TRAPPING (LOW FIELD)



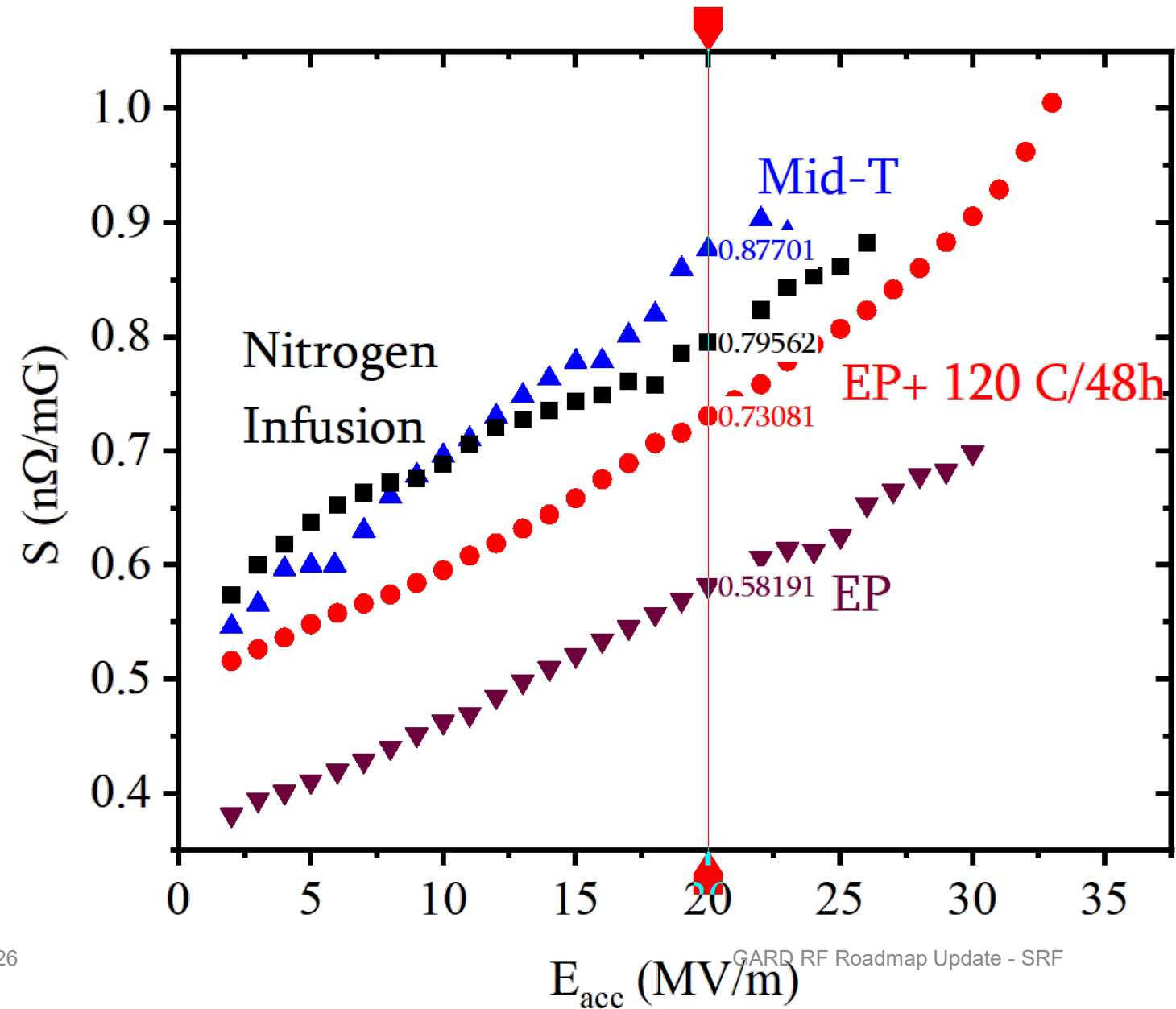
Flux trapping sensitivity depends on

- Mean free path
- Pinning strength/type
- Frequency
- Orientation of flux lines with respect to rf field

P. Dhakal et al., PRAB, 23, 023102 (2020)

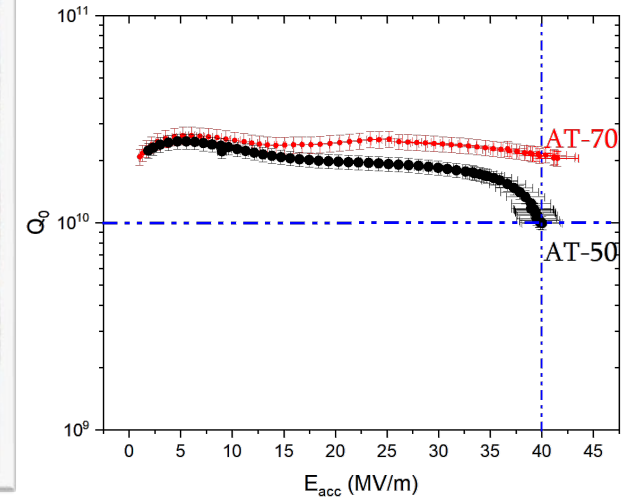
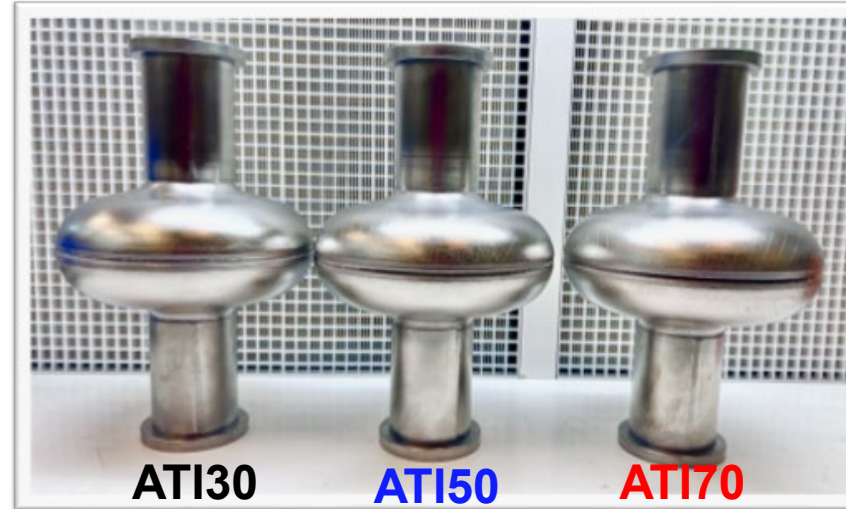
A. Gurevich, SUST, 30, 034004 (2017)

FLUX TRAPPING-FIELD DEPENDENCE



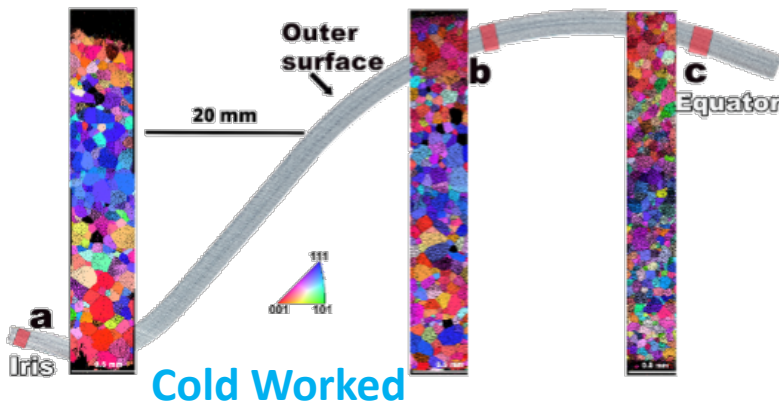
At operating gradient, the benefit of high Q_0 is minimized due to large flux trapping sensitivity

FLUX EXPULSION/TRAPPING/RECRYSTALLIZATION

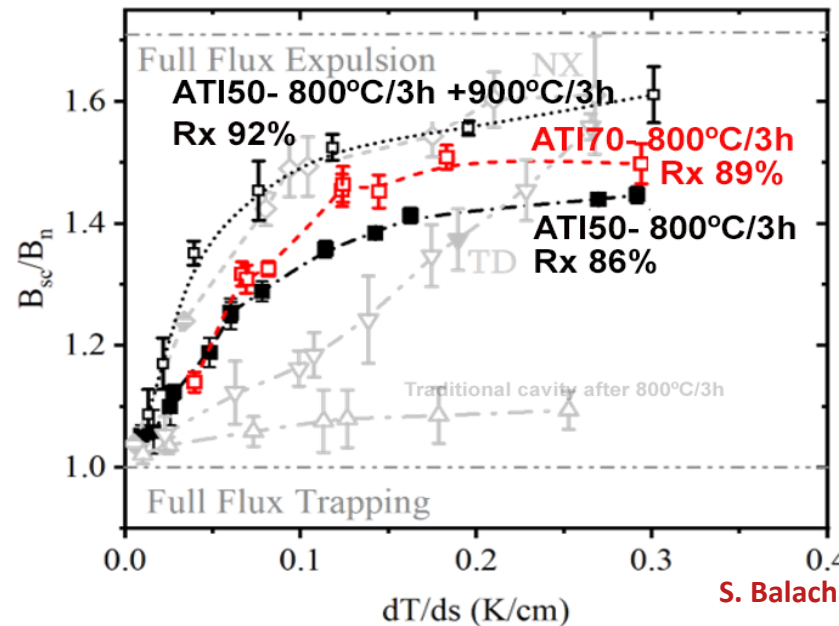


Traditional

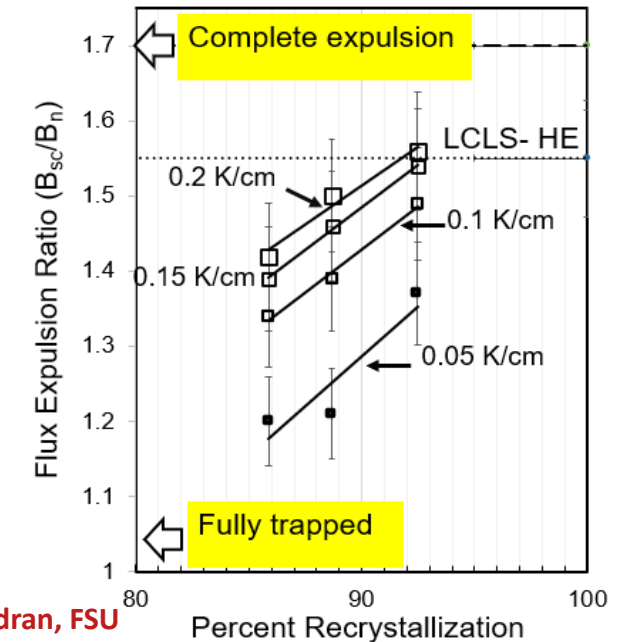
Cavities fabricated from cold-worked Nb sheets, followed by heat treatment at 800°C shown to **Improved flux expulsion** compared to traditional methods



Cold Worked

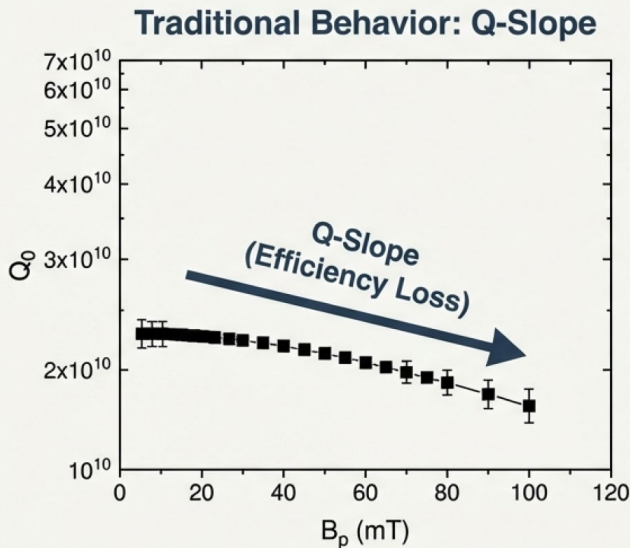


S. Balachandran, FSU

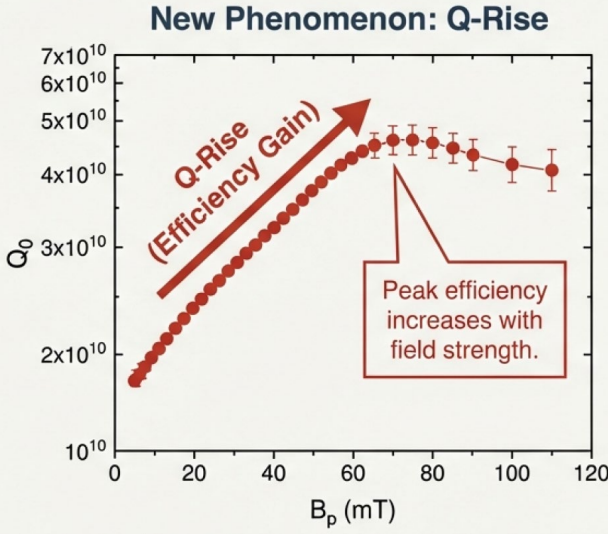


**The main source of
surface resistance at operating gradient is
due to residual flux trapping
during cooldown**

Q₀-RISE & FREQUENCY DEPENDENCE



The Threshold



No Q-Rise observed
(e.g., 650 MHz)

900 MHz
2.0 K

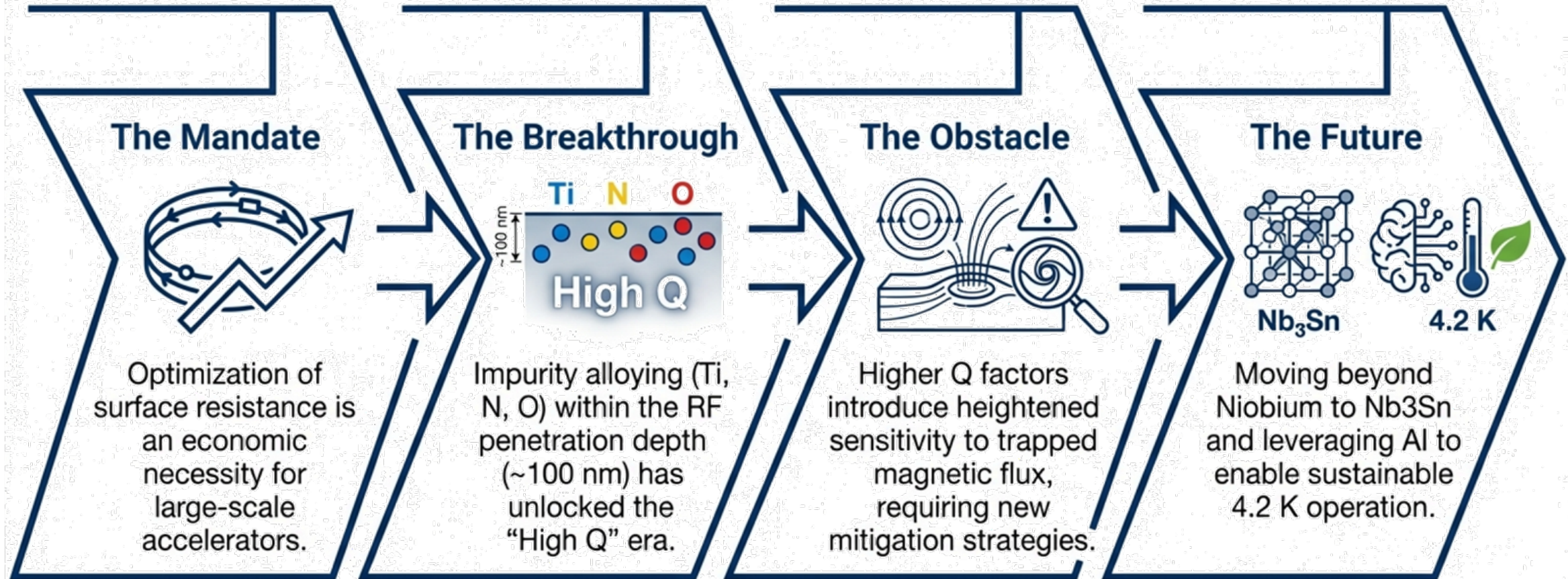
Q-Rise Enabled
(e.g., 1.3 GHz)

Theoretical Model: Non-Equilibrium Superconductivity

A race between the RF drive and electron relaxation.

Gurevich, SUST (2023)
Kubo & Gurevich, PRB 100, 064522 (2019)
Kaplan et al., PRB 14, 4854 (1976)

The Path to Next-Generation SRF Performance



Mastering nanoscale surface physics to enable miles long discovery

Questions?